

R07DS0989EJ0100

Rev.1.00

Dec 25, 2012

μ**PA2826T1S**

N-channel MOSFET

20 V , 27 A , 4.3 m Ω

Description

The μ PA2826T1S is N-channel MOS Field Effect Transistor designed for power management applications of portable equipment .

Features

- $V_{DSS} = 20 V (T_A = 25^{\circ}C)$
- Low on-state resistance
 - ---- $R_{DS(on)} = 4.3 \text{ m}\Omega \text{ MAX}. (V_{GS} = 8.0 \text{ V}, I_D = 13.5 \text{ A})$
- 2.5 V Gate-drive available
- Small & thin type surface mount package with heat spreader
- Pb-free and Halogen free



HWSON-8

Ordering Information

Part No.	LEAD PLATING	PACKING	Package
μ PA2826T1S-E2-AT*1	Pure Sn(Tin)	Tape 5000 p/reel	HWSON-8
		Tape 5000 p/Teel	0.022 g TYP.

Note: *1. Pb-free (This product does not contain Pb in external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

ltem	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	20	V
Gate to Source Voltage ($V_{DS} = 0 V$)	V _{GSS}	±12	V
Drain Current (DC) ($T_C = 25^{\circ}C$)	I _{D(DC)}	±27	A
Drain Current (pulse) *1	I _{D(pulse)}	±81	A
Total Power Dissipation *2	P _{T1}	1.5	W
Total Power Dissipation (PW = 10 sec) *2	P _{T2}	3.8	W
Total Power Dissipation ($T_c = 25^{\circ}C$)	P _{T3}	20	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Thermal Resistance

Channel to Ambient Thermal Resistance *2	R _{th(ch-A)}	83.3	°C/W
Channel to Case(Drain) Thermal Resistance	R _{th(ch-C)}	6.25	°C/W

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

*2. Mounted on a glass epoxy board of 25.4 mm x 25.4 mm x 0.8 mmt

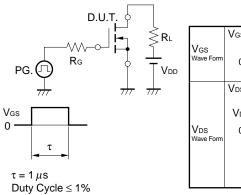


Electrical Characteristics ($T_A = 25^{\circ}C$)

Item	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$
Gate Leakage Current	I _{GSS}			±10	μA	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	V _{GS(off)}	0.5		1.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	25			S	$V_{DS} = 10 \text{ V}, I_{D} = 6.8 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		3.4	4.3	mΩ	$V_{GS} = 8.0 \text{ V}, I_D = 13.5 \text{ A}$
Resistance *1	R _{DS(on)2}		3.9	4.8	mΩ	$V_{GS} = 4.5 \text{ V}, I_D = 13.5 \text{ A}$
	R _{DS(on)3}		5.4	9.9	mΩ	$V_{GS} = 2.5 \text{ V}, I_D = 6.8 \text{ A}$
Input Capacitance	C _{iss}		3610		pF	V _{DS} = 10 V,
Output Capacitance	Coss		1230		pF	$V_{GS} = 0 V,$
Reverse Transfer Capacitance	C _{rss}		1130		pF	f = 1 MHz
Turn-on Delay Time	t _{d(on)}		50		ns	$V_{DD} = 10 \text{ V}, I_D = 13.5 \text{ A},$
Rise Time	t _r		94		ns	$V_{GS} = 4.0 V,$
Turn-off Delay Time	t _{d(off)}		120		ns	R _G = 10 Ω
Fall Time	t _f		120		ns	
Total Gate Charge	Q _G		37		nC	V _{DD} = 10 V,
Gate to Source Charge	Q _{GS}		7		nC	$V_{GS} = 4.0 V,$
Gate to Drain Charge	Q _{GD}		18		nC	I _D = 27 A
Body Diode Forward Voltage *1	V _{F(S-D)}		0.82		V	$I_F = 27 \text{ A}, V_{GS} = 0 \text{ V}$
Reverse Recovery Time	t _{rr}		73		ns	$I_F = 27 \text{ A}, V_{GS} = 0 \text{ V},$
Reverse Recovery Charge	Q _{rr}		70		nC	di/dt = 100 A/µs

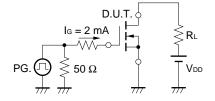
Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME



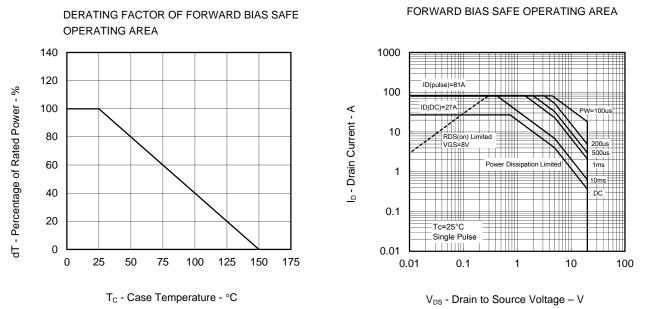
Vgs 90% 0 -----Vgs VDS 90% 190% Vds 10% 10% 0 td(on) tr td(off) tf toff ton

TEST CIRCUIT 2 GATE CHARGE

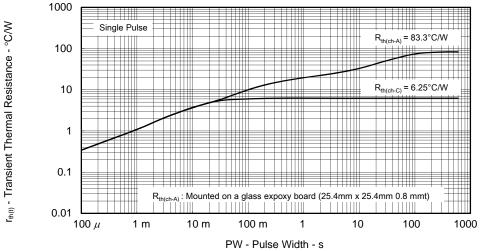




TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

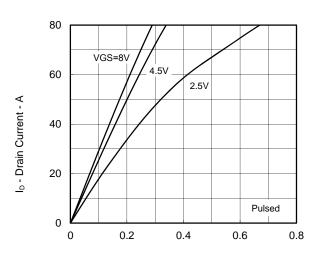


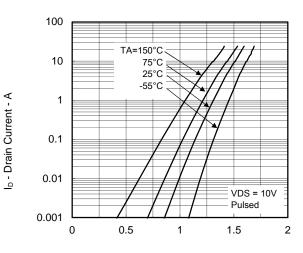


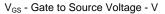


DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

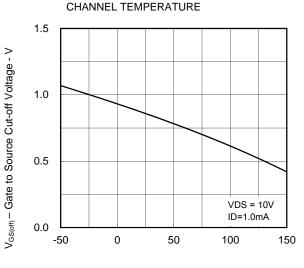








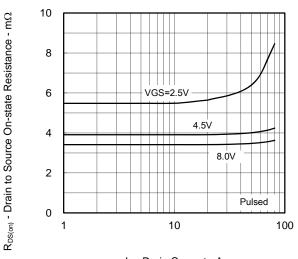




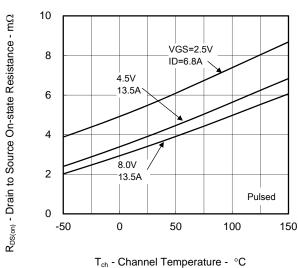
GATE TO SOURCE CUT-OFF VOLTAGE vs.

T_{ch} - Channel Temperature - °C

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



I_D - Drain Current - A



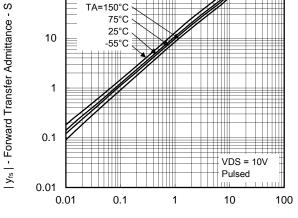
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

75°C 25°C 10 -55°C

TA=150°C

CURRENT

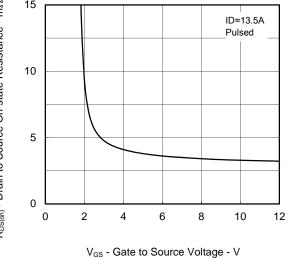
100



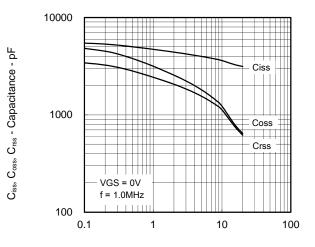
FORWARD TRANSFER ADMITTANCE vs. DRAIN

I_D - Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} - Drain to Source Voltage - V

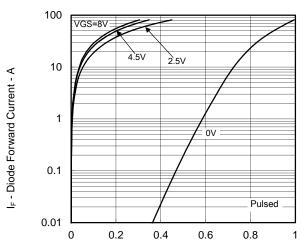


¹⁵ $R_{\text{DS(on)}}$ - Drain to Source On-state Resistance - $m\Omega$

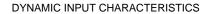
1000 VDD = 10V VGS = 4.0V RG = 10Ω td(on),tr,td(off),tr - Switching Time - ns tf td(off) 100 tr td(on) 10 0.1 10 100 1

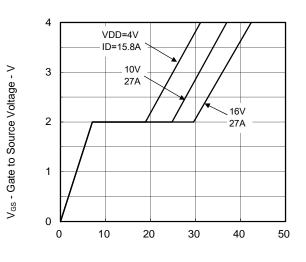
SWITCHING CHARACTERISTICS

I_D - Drain Current - A



 $V_{F(S-D)}$ - Source to Drain Voltage - V





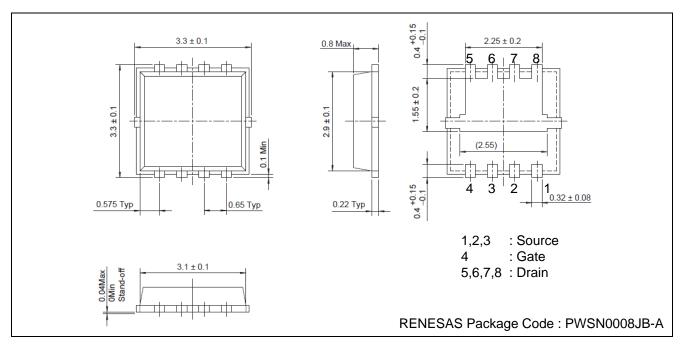
Q_G - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

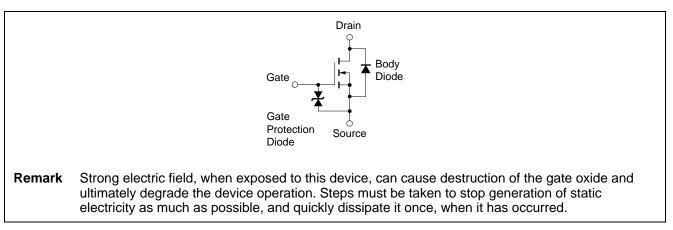


Package Drawings (Unit: mm)

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Equivalent Circuit





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